

GSDSBAT54XV2

Schottky Barrier Diode

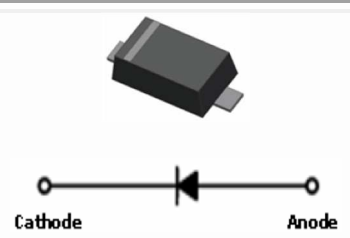
Product Description

Schottky Barrier Diode 200mW / 30V

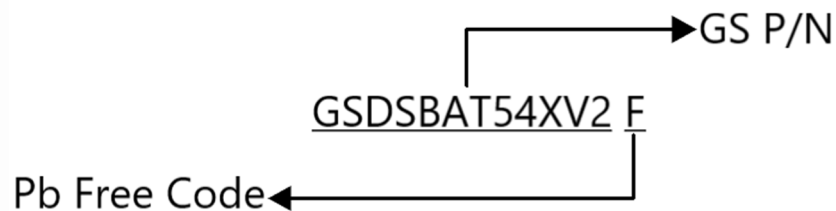
Features

- Low Forward Voltage Drop
- Extremely Small SOD-523 Package
- Flat Lead SOD-523 Small Outline Plastic Package
- Surface Device Type Mounting
- RoHS Compliant
- Green EMC
- Matte Tin(Sn) Lead Finish
- Band Indicate Cathode

Marking Information

Part Number	Package	Part Marking	Equivalent Circuit diagram
GSDSBAT54XV2F	SOD-523	5B	

Ordering Information



Part Number	Package	Quantity
GSDSBAT54XV2F	SOD-523	3000 PCS

Absolute Maximum Ratings

($T_A=25^{\circ}\text{C}$ Unless otherwise noted)

Symbol	Parameter	Value	Unit
P_D	Power Dissipation	200	mW
V_{RRM}	Repetitive Peak Reverse Voltage	30	V
V_R	Maximum DC Blocking Voltage	30	V
T_J	Operating Junction Temperature	+125	$^{\circ}\text{C}$
T_{STG}	Storage Temperature Range	-65 to +125	$^{\circ}\text{C}$
$I_{F(AV)}$	Average Forward Rectified Current	200	mA
I_{FSM}	Forward current surge peak	4	A

These ratings are limiting values above which the serviceability of the diode may be impaired.

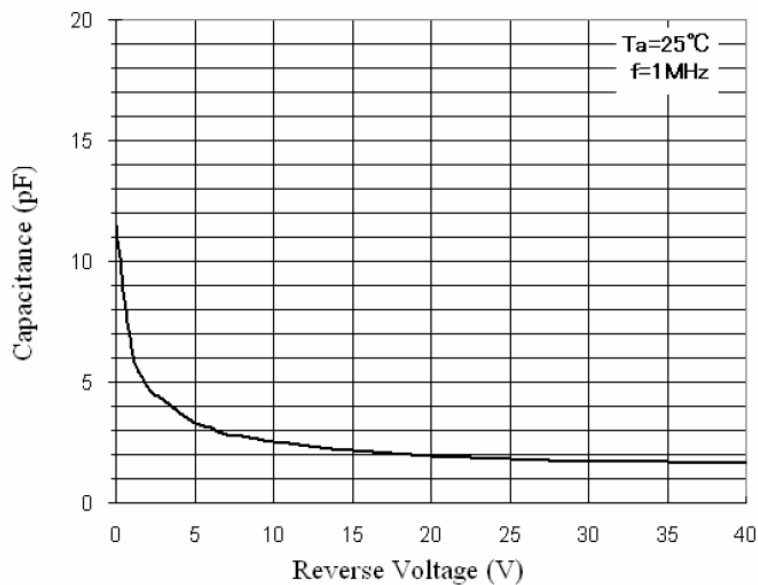
Electrical Characteristics

($T_A=25^{\circ}\text{C}$ Unless otherwise noted)

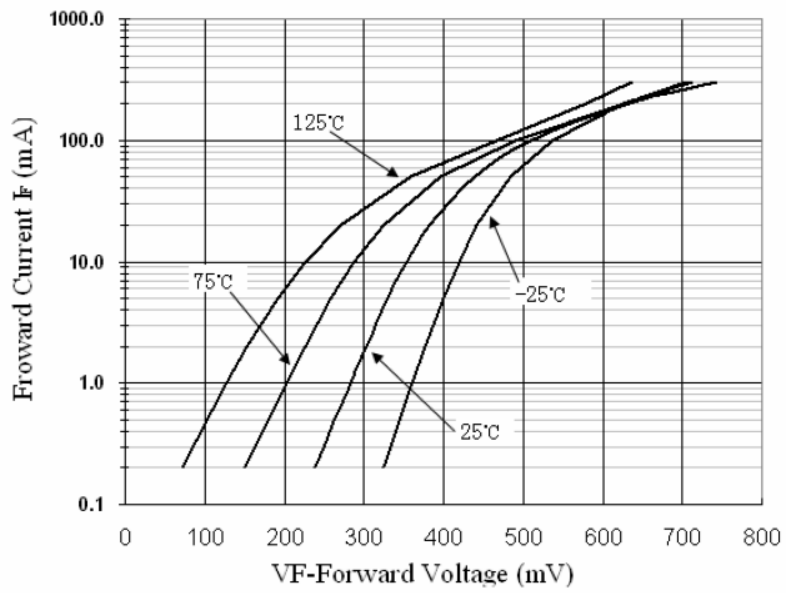
Symbol	Parameter	Test Condition	Min	Max	Unit
B_V	Breakdown Voltage	$I_R = 10\mu\text{A}$	30	-	V
I_R	Reverse Current	$V_R = 25\text{V}$	-	2	μA
V_F	Forward Voltage	$I_F = 0.1\text{mA}$	-	0.24	V
		$I_F = 1\text{mA}$	-	0.32	
		$I_F = 10\text{mA}$	-	0.40	
		$I_F = 30\text{mA}$	-	0.50	
		$I_F = 100\text{mA}$	-	0.80	
T_{RR}	Reverse Recovery Time	$I_F = I_R = 10\text{mA}$ $R_L = 100\Omega$ $I_{RR} = 1\text{mA}$	-	5	nS
C	Capacitance	$V_R = 1\text{V}, f = 1\text{MHz}$	-	10	pF

Typical Characteristics

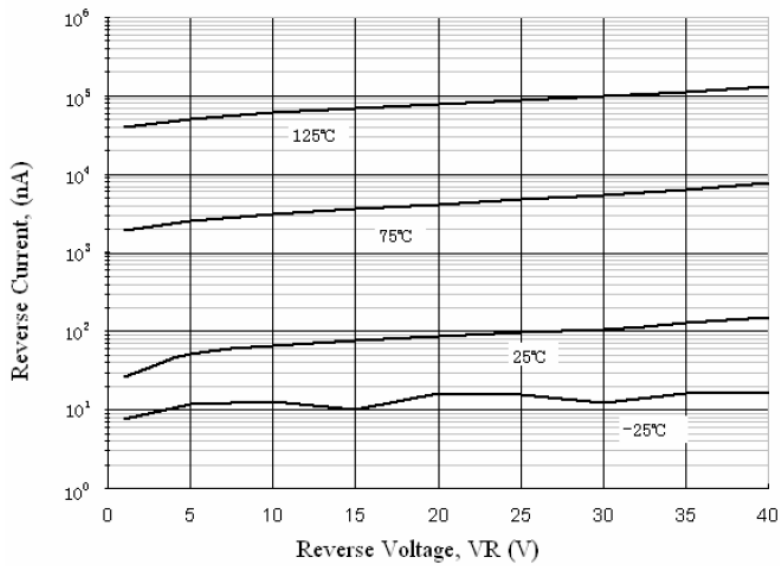
Total Capacitance



Forward Voltage vs Ambient Temperature

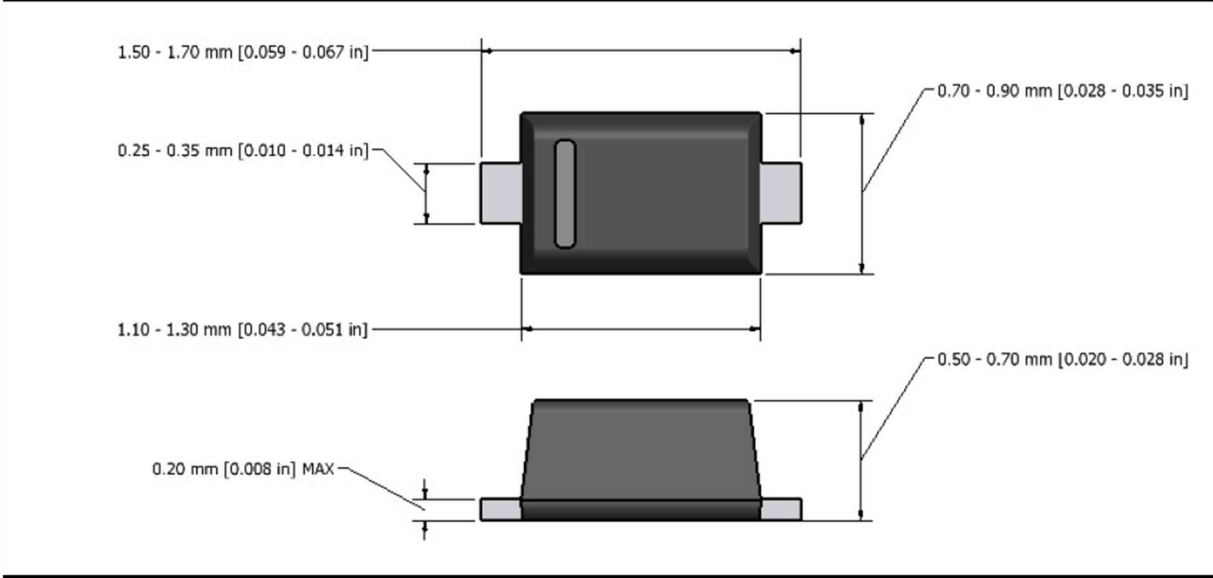


Reverse Current vs Reverse Voltage



Package Dimension

SOD-523







NOTICE

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